

### STD830CP20

### Complementary transistor pair in a single package

Preliminary data

#### **Features**

- Low V<sub>CE(sat)</sub>
- Simplified circuit design
- Reduced component count
- Low spread of dynamic parameters

### **Applications**

■ Compact fluorescent lamp (CFL) 110 V mains

### **Description**

The STD830CP20 is a hybrid complementary pair of power bipolar transistors manufactured by using the high voltage multi-epitaxial planar technology for high switching speeds and medium voltage capability.

The STD830CP20 is housed in dual island DIP-8 package with separated terminals for higher assembly flexibility, specifically recommended to be used in a new solution for compact fluorescent lamp (CFL).

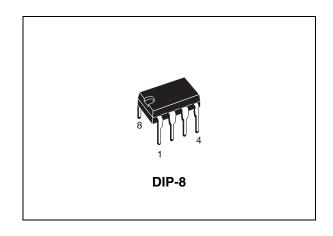


Figure 1. Internal schematic diagram

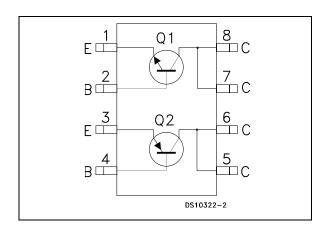


Table 1. Device summary

Order code	Marking	Package	Packing
STD830CP20	D830CP20	DIP-8	Tube

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STD830CP20 **Electrical ratings** 

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Table 2. **Absolute maximum ratings** 

Symbol	Dawa wa aka w	Va	Value	
	Parameter	NPN	PNP	- Unit
V <sub>CBO</sub>	Collector-base voltage (I <sub>E</sub> = 0)	400	300	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0) 200		00	V
V <sub>EBO</sub>	Emitter-base voltage ( $I_C = 0$ , $I_b = 1.5$ A, $t_p < 10$ ms)	V <sub>(BR</sub>	V <sub>(BR)EBO</sub>	
I <sub>C</sub>	Collector current	3		Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	6		Α
I <sub>B</sub>	Base current		1.5	
I <sub>BM</sub>	Base peak current (t <sub>P</sub> < 1 ms)	3		Α
P <sub>tot</sub>	Total dissipation at T <sub>amb</sub> = 25 °C single transistor	TBD		W
P <sub>tot</sub>	Total dissipation at T <sub>amb</sub> = 25 °C both transistors	TBD		W
T <sub>stg</sub>	Storage temperature	-65 to 150		°C
T <sub>J</sub>	Max. operating junction temperature	150		°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-amb</sub> <sup>(1)</sup>	Thermal resistance junction-ambient (Single transistor)	TBD	°C/W
R <sub>thj-amb</sub> <sup>(1)</sup>	Thermal resistance junction-ambient (Both transistors)	TBD	°C/W

<sup>1.</sup> When mounted on 1 inch square pad of 2 oz. copper,  $t \le 10$  sec.

Note: For PNP types voltage and current values are negative



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### 2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$ 

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	For NPN: $V_{CE} = 400 \text{ V}$ $V_{CE} = 400 \text{ V}$ $V_{CE} = 400 \text{ V}$ $V_{CE} = 125^{\circ}$ $V_{CE} = 300 \text{ V}$			0.1 0.5 0.1 0.5	mA mA mA
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 10 mA For NPN: For PNP:	9		18 12	V V
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 5 mA	200			V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	$I_C = 0.5 \text{ A}$ $I_B = 0.05 \text{ A}$ $I_C = 0.7 \text{ A}$ $I_B = 0.1 \text{ A}$			400 400	mV mV
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	$I_C = 0.5 \text{ A}$ $I_B = 0.1 \text{ A}$ $I_C = 1 \text{ A}$ $I_B = 0.2 \text{ A}$			1 1.1	V V
h <sub>FE</sub> <sup>(1)</sup>	DC current gain		V 22		36	
t <sub>r</sub> t <sub>s</sub>	Resistive load Rise time Storage time Fall time	$I_C = 0.7 \text{ A}$ $V_{CC} = 150$ $I_{B1} = 0.14 \text{ A}$ $I_{B2} = -0.14$ $t_p = 30  \mu \text{s}$		80 1.2 80		ns µs ns
t <sub>s</sub>	Inductive load Storage time Fall time	$\begin{split} I_C &= 1 \text{ A} & I_{B1} = 0.1 \\ V_{BE(off)} &= -5 \text{ V} & R_{BB} = 0 \\ V_{clamp} &= 150 \text{ V} & L = 1 \text{ mHz} \end{split}$		120 50		ns ns

<sup>1.</sup> Pulsed: Pulse duration = 300  $\mu$ s, duty cycle  $\leq$  1.5 %

Note: For PNP types voltage and current values are negative

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## 3 Package mechanical data

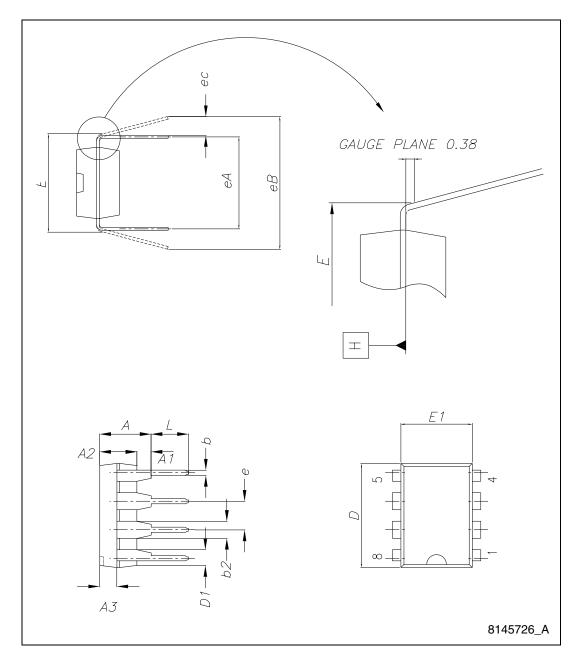
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Table 5. DIP-8 mechanical data

Dim.		mm.	
	Min	Тур.	Max.
Α			4.80
A1	0.50		
A2	3.10		3.50
A3	1.40		1.60
b	0.38		0.55
b1	0.38		0.51
b2	1.47		1.57
b3	0.89		1.09
С	0.21		0.35
c1	0.20		0.30
D	9.10		9.30
D1	0.13		
E	7.62		8.25
E1	6.25		6.45
е		2.54	
eA		7.62	
eB	7.62		10.90
eC	0		1.52
L	2.92		3.81

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Figure 2. Drawing dimension DIP-8



STD830CP20 **Revision history** 

## www.DataSheet4U.com 4 Revision history

**Document revision history** Table 6.

Date	Revision	Changes
26-May-2009	1	Initial release.



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